

DMTH6004SPS

60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 9)
60V	$3.1 \text{m}\Omega$ @ $V_{GS} = 10V$	100A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

POWERDI®5060-8

Applications

- DC Motor Control
- Synchronous Rectification
- DC/DC Converters

Features

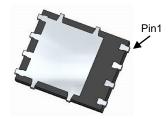
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable And Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_q Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH6004SPSQ)

Mechanical Data

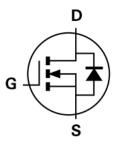
- Case: POWERDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.097 grams (Approximate)



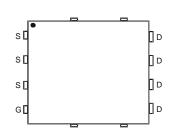




Bottom View



Internal Schematic



Top View Pin Configuration

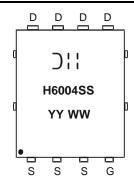
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6004SPS-13	POWERDI®5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃¦¦ = Manufacturer's Marking H6004SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 14 = 2014) WW = Week (01 to 53)



Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	ΙD	25 21	А
Continuous Drain Current (Note 6)	$T_{C} = +25^{\circ}C$ (Note 9) $T_{C} = +100^{\circ}C$	Ι _D	100 100	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	200	Α
Avalanche Current, L = 0.2mH		I _{AS}	45	Α
Avalanche Energy, L = 0.2mH		E _{AS}	200	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_{D}	167	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	0.9	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	l	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	l	2.5	3.1	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V_{SD}	l	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		4556	_		$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	1383	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	105.2	_			
Gate Resistance	Rg	_	0.66	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	95.4			V 20V I 00A	
Gate-Source Charge	Q _{gs}	_	21.6	_	nC	$V_{DD} = 30V, I_D = 90A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q _{gd}	_	20.4	_			
Turn-On Delay Time	t _{D(ON)}	_	13.2	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	11.7	_			
Turn-Off Delay Time	t _{D(OFF)}	_	31	_	ns		
Turn-Off Fall Time	t _F	_	12	_			
Body Diode Reverse Recovery Time	t _{RR}		50.5		ns	L 500 di/dt 4000/us	
Body Diode Reverse Recovery Charge	Q _{RR}	_	80.8	_	nC	$I_F = 50A$, di/dt = 100A/ μ s	

Notes: 5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.

- willist operating in a steady state.

 6. Thermal resistance from junction to soldering point (on the exposed drain pad).

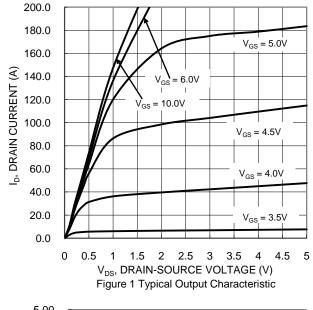
 7. Short duration pulse test used to minimize self-heating effect.

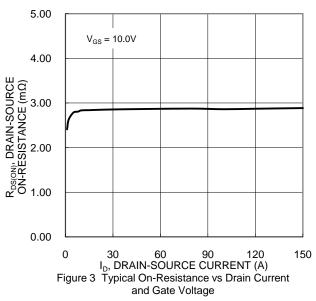
 8. Guaranteed by design. Not subject to product testing.

 9. Package limited.









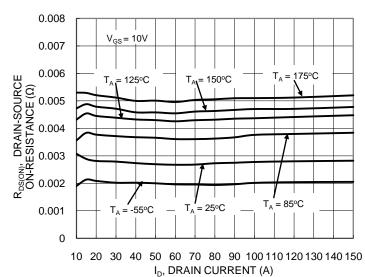
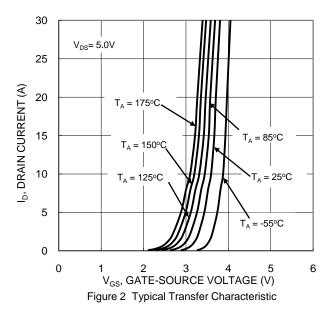
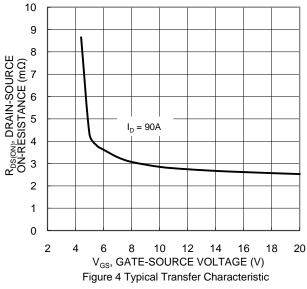


Figure 5 Typical On-Resistance vs Drain Current and Temperature





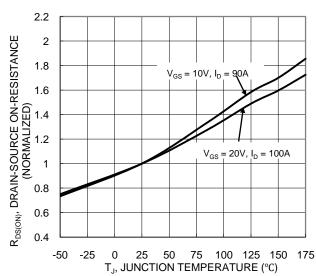
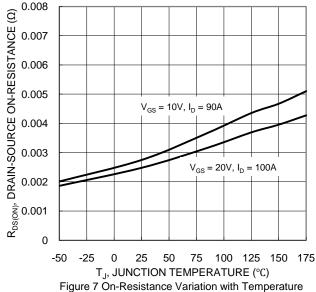
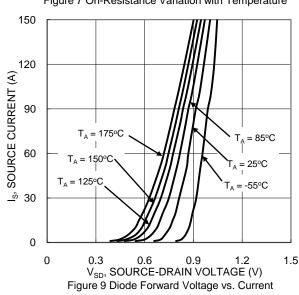


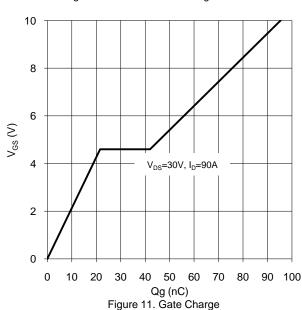
Figure 6 On-Resistance Variation with Temperature











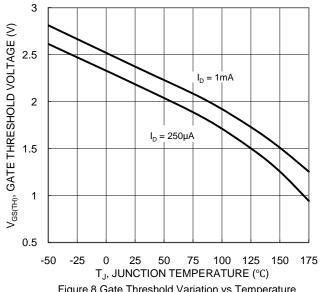
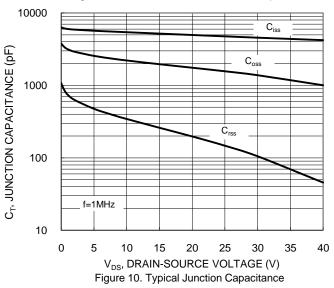
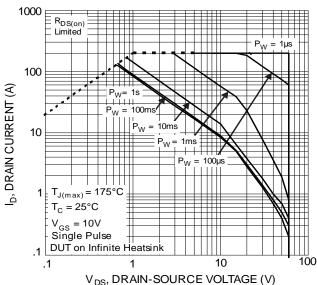
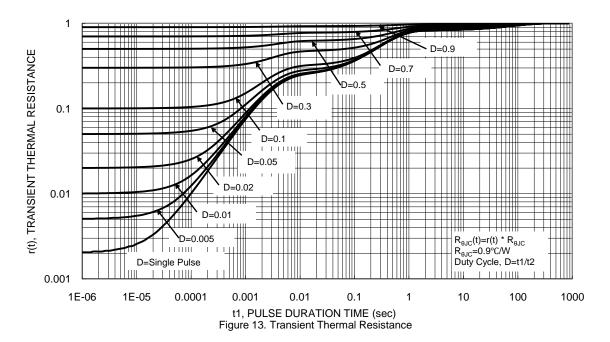


Figure 8 Gate Threshold Variation vs Temperature







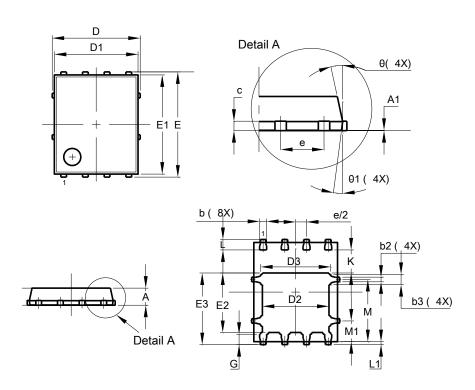




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI®5060-8

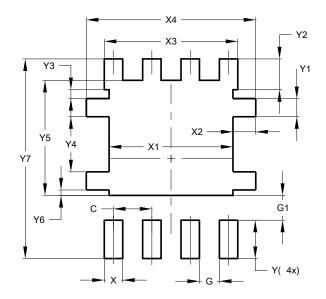


POWERDI®5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90 4.30		4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39 4.1			
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	_		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
М1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI®5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
Х	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Y	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
Y7	6.610				



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